



INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(51) International Patent Classification ⁶ : B23K 20/00	A1	(11) International Publication Number: WO 98/29213 (43) International Publication Date: 9 July 1998 (09.07.98)
(21) International Application Number: PCT/US97/23847 (22) International Filing Date: 22 December 1997 (22.12.97) (30) Priority Data: 08/780,166 26 December 1996 (26.12.96) US (71) Applicant: JOHNSON MATTHEY ELECTRONICS, INC. [US/US]; East 15128 Euclid Avenue, Spokane, WA 99216 (US). (72) Inventor: KARDOKUS, Janine, K.; East 18122 Monte Vista Court, Otis Orchards, WA 99027 (US). (74) Agent: GIOIA, Vincent, G.; Christie, Parker & Hale, LLP, P.O. Box 7068, Pasadena, CA 91109-7068 (US).	(81) Designated States: CN, JP, KR, SG, European patent (AT, BE, CH, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE). Published <i>With international search report.</i> <i>Before the expiration of the time limit for amending the claims and to be republished in the event of the receipt of amendments.</i>	

(54) Title: **METHOD OF MAKING HIGH PURITY COPPER SPUTTERING TARGETS**

(57) Abstract

Described is a method of making high purity copper sputtering target. The method avoids melting and casting and involves stacking segments of high purity copper plates, and heating, forging and annealing to produce a diffusion bonded unitary structure.

